

# PMEG6030ETP

High-temperature 60 V, 3 A Schottky barrier rectifier

15 October 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

### 1.2 Features and benefits

- Average forward current:  $I_{F(AV)} \leq 3$  A
- Reverse voltage:  $V_R \leq 60$  V
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature  $T_j \leq 175$  °C

### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$I_F$	forward current	$T_{sp} = 160$ °C		-	-	4.2	A
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; $f = 20$ kHz; $T_{amb} \leq 80$ °C; square wave	[1]	-	-	3	A
		$\delta = 0.5$ ; $f = 20$ kHz; $T_{sp} \leq 165$ °C; square wave		-	-	3	A
$V_R$	reverse voltage	$T_j = 25$ °C		-	-	60	V
$V_F$	forward voltage	$I_F = 3$ A; $T_j = 25$ °C		-	460	530	mV
$I_R$	reverse current	$T_j = 25$ °C; $V_R = 60$ V; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; pulsed		-	80	200	$\mu$ A



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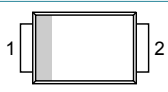



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{rr}$	reverse recovery time	$I_R = 0.5\text{ A}$ ; $I_F = 0.5\text{ A}$ ; $I_{R(\text{meas})} = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$	-	12	-	ns

[1] Device mounted on a ceramic Printed-Circuit Board (PCB),  $\text{Al}_2\text{O}_3$ , standard footprint.

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	 <p>SOD128</p>	 <p>sym001</p>
2	A	anode		

[1] The marking bar indicates the cathode.

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG6030ETP	SOD128	plastic surface-mounted package; 2 leads	SOD128

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG6030ETP	DA

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_R$	reverse voltage	$T_j = 25\text{ °C}$	-	60	V	
$I_F$	forward current	$T_{sp} = 160\text{ °C}$	-	4.2	A	
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; $f = 20\text{ kHz}$ ; $T_{amb} \leq 80\text{ °C}$ ; square wave	[1]	-	3	A
		$\delta = 0.5$ ; $f = 20\text{ kHz}$ ; $T_{sp} \leq 165\text{ °C}$ ; square wave	-	-	3	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 8\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; square wave	-	50	A	

Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	750	mW
			[3]	-	1250	mW
			[1]	-	2500	mW
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

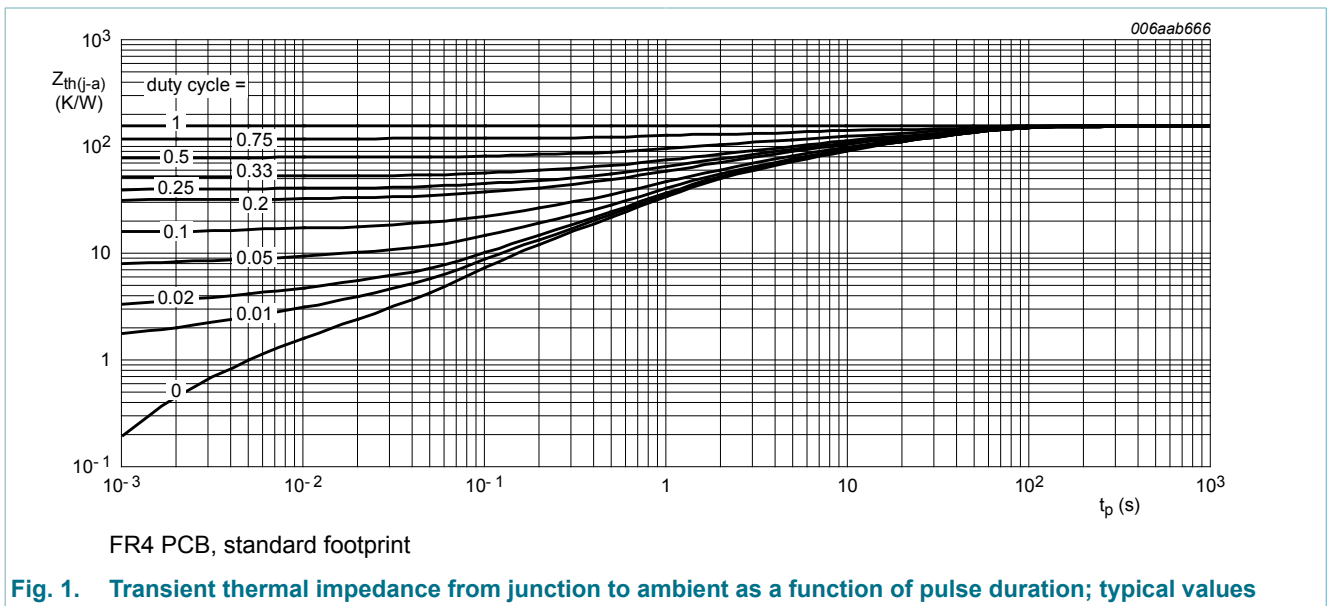
- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

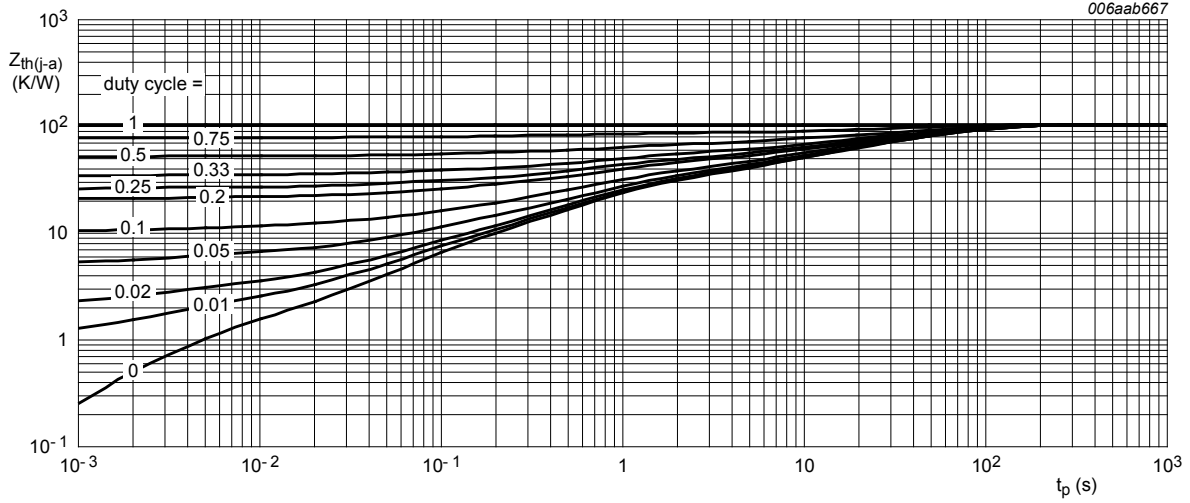
## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1][2]	-	-	200	K/W
			[1][3]	-	-	120	K/W
			[1][4]	-	-	60	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	12	K/W

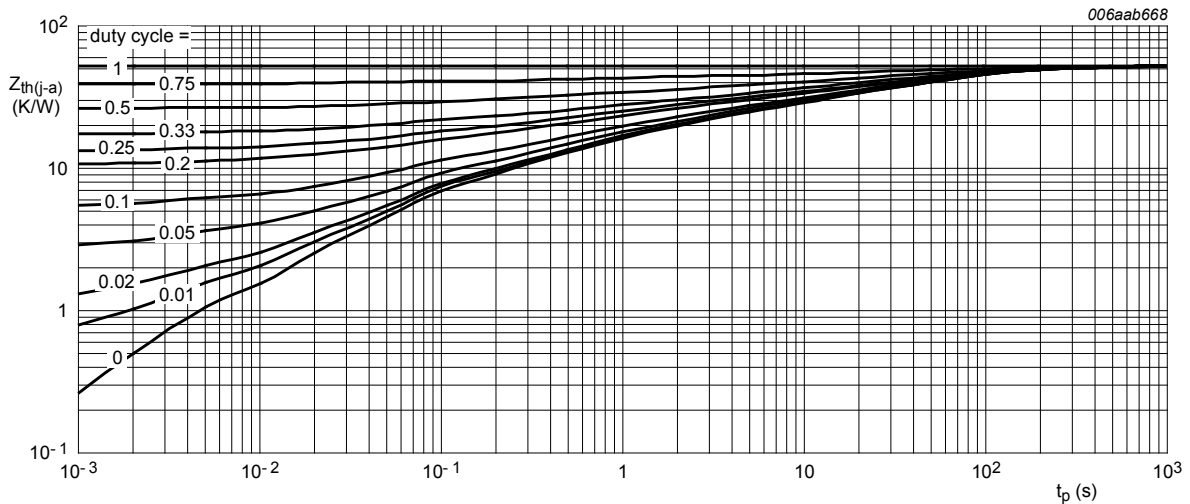
- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.





FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 7. Characteristics

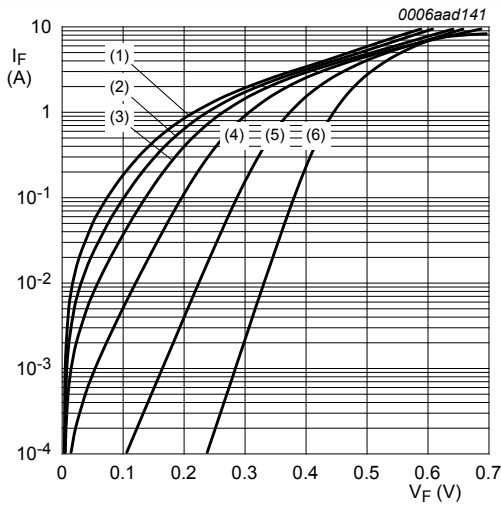
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 0.1 A; T <sub>j</sub> = 25 °C	-	290	330	mV
		I <sub>F</sub> = 0.5 A; T <sub>j</sub> = 25 °C	-	340	400	mV
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 25 °C	-	380	440	mV
		I <sub>F</sub> = 1.5 A; T <sub>j</sub> = 25 °C	-	400	470	mV
		I <sub>F</sub> = 2 A; T <sub>j</sub> = 25 °C	-	430	500	mV
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C	-	460	530	mV

## High-temperature 60 V, 3 A Schottky barrier rectifier

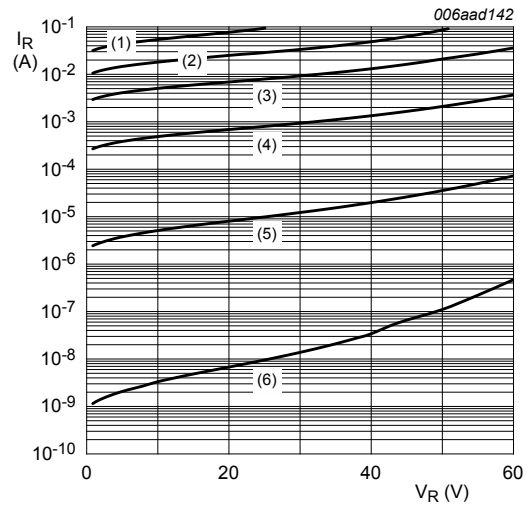
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$I_F = 3 \text{ A}; T_j = -40 \text{ }^\circ\text{C}$	-	510	590	mV
		$I_F = 3 \text{ A}; T_j = 125 \text{ }^\circ\text{C}$	-	405	480	mV
		$I_F = 3 \text{ A}; T_j = 150 \text{ }^\circ\text{C}$	-	390	460	mV
		$I_F = 3 \text{ A}; T_j = 175 \text{ }^\circ\text{C}$	-	370	450	mV
$I_R$	reverse current	$V_R = 5 \text{ V}; T_j = 25 \text{ }^\circ\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$ ; pulsed	-	4	-	$\mu\text{A}$
		$V_R = 10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$ ; pulsed	-	5	-	$\mu\text{A}$
		$V_R = 60 \text{ V}; T_j = 25 \text{ }^\circ\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$ ; pulsed	-	80	200	$\mu\text{A}$
		$V_R = 60 \text{ V}; T_j = -40 \text{ }^\circ\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$ ; pulsed	-	0.5	10	$\mu\text{A}$
		$V_R = 60 \text{ V}; T_j = 125 \text{ }^\circ\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$ ; pulsed	-	45	150	mA
$C_d$	diode capacitance	$V_R = 1 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$	-	360	-	pF
		$V_R = 10 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$	-	120	-	pF
$t_{rr}$	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(\text{meas})} = 0.1 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	12	-	ns
$V_{FRM}$	peak forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 40 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C}$	-	425	-	mV

High-temperature 60 V, 3 A Schottky barrier rectifier



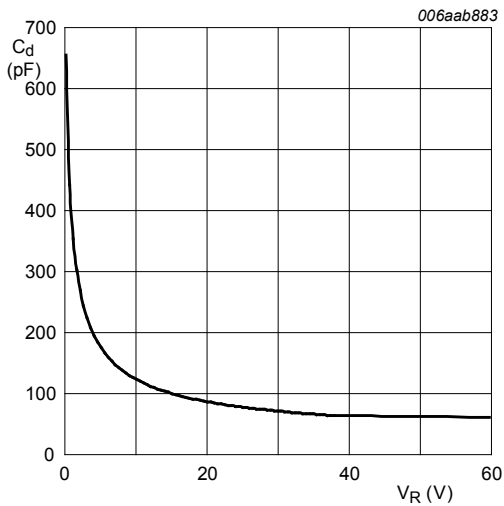
- (1)  $T_j = 175\text{ °C}$
- (2)  $T_j = 150\text{ °C}$
- (3)  $T_j = 125\text{ °C}$
- (4)  $T_j = 85\text{ °C}$
- (5)  $T_j = 25\text{ °C}$
- (6)  $T_j = -40\text{ °C}$

Fig. 4. Forward current as a function of forward voltage; typical values



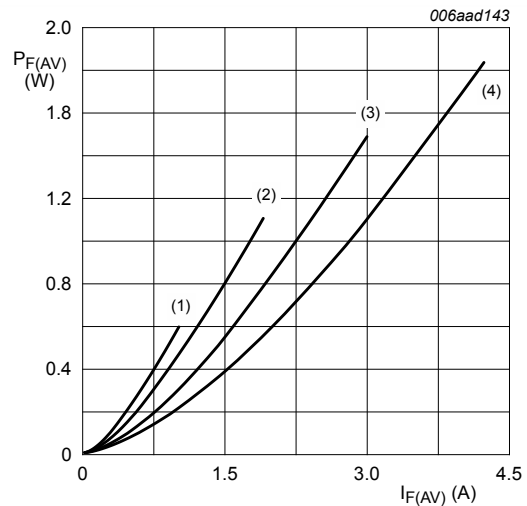
- (1)  $T_j = 175\text{ °C}$
- (2)  $T_j = 150\text{ °C}$
- (3)  $T_j = 125\text{ °C}$
- (4)  $T_j = 85\text{ °C}$
- (5)  $T_j = 25\text{ °C}$
- (6)  $T_j = -40\text{ °C}$

Fig. 5. Reverse current as a function of reverse voltage; typical values



$f = 1\text{ MHz}; T_{amb} = 25\text{ °C}$

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



- $T_j = 175\text{ °C}$
- (1)  $\delta = 0.1$
- (2)  $\delta = 0.2$
- (3)  $\delta = 0.5$
- (4)  $\delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values

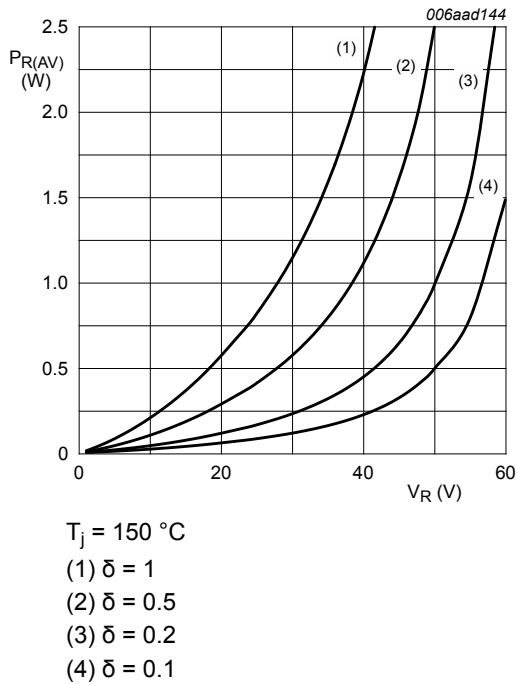


Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values

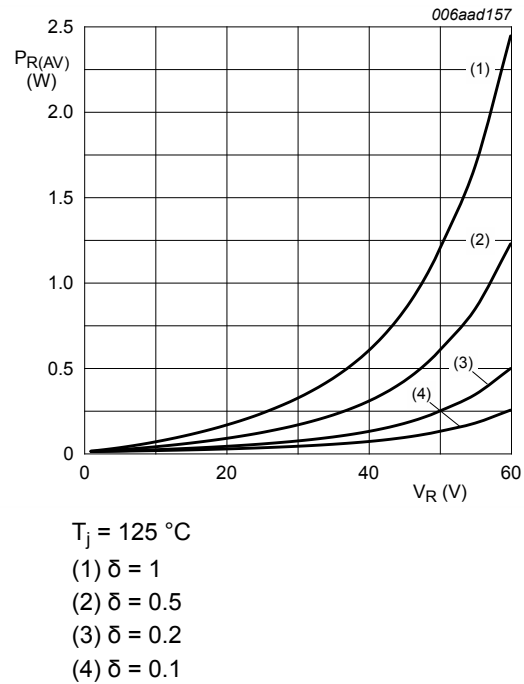


Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values

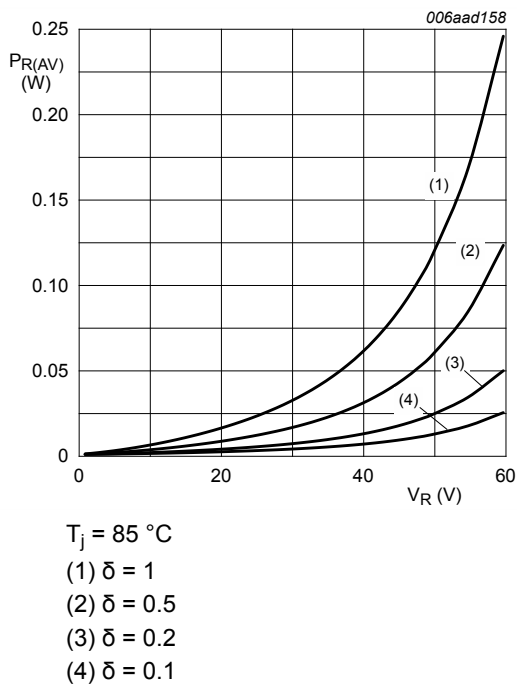


Fig. 10. Average reverse power dissipation as a function of reverse voltage; typical values

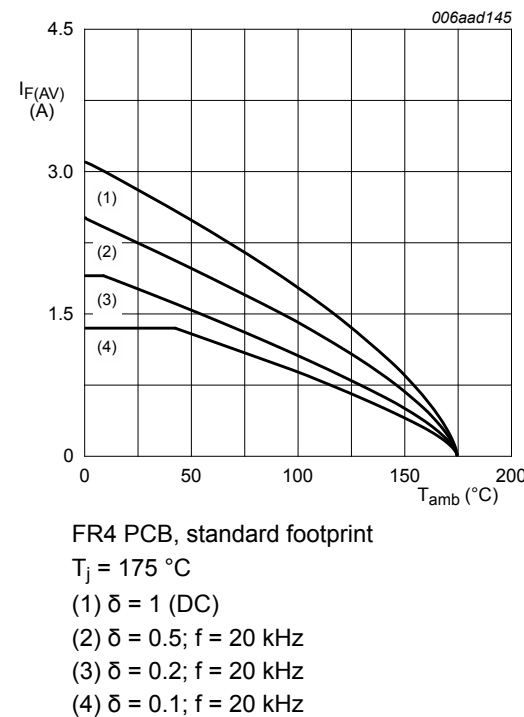
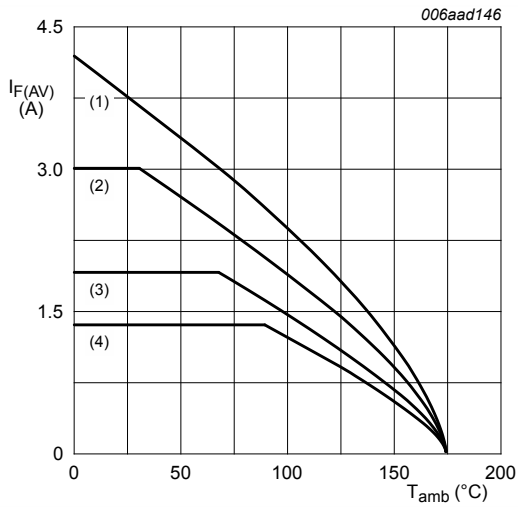
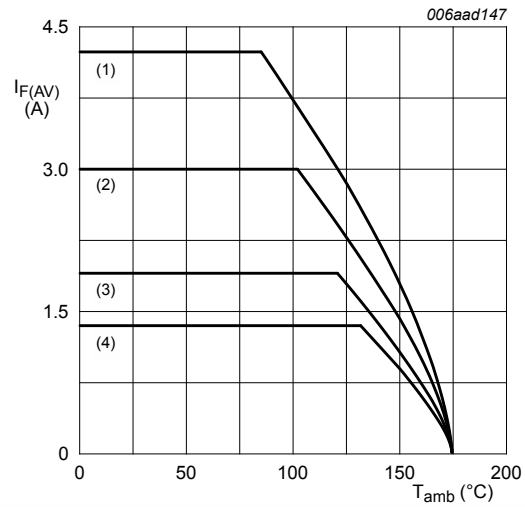


Fig. 11. Average forward current as a function of ambient temperature; typical values



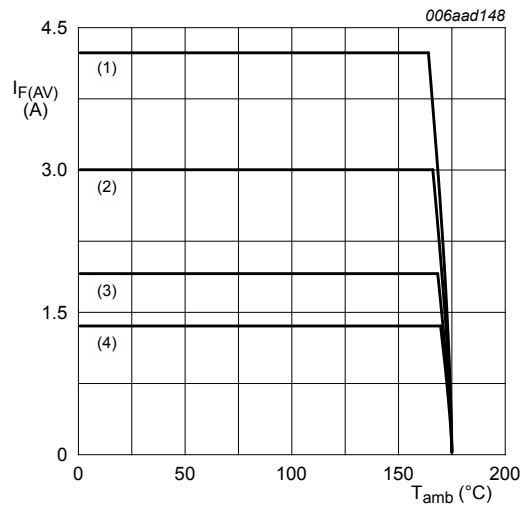
FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>  
 $T_j = 175\text{ °C}$   
 (1)  $\delta = 1$  (DC)  
 (2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$   
 (3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$   
 (4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

**Fig. 12. Average forward current as a function of ambient temperature; typical values**



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint  
 $T_j = 175\text{ °C}$   
 (1)  $\delta = 1$  (DC)  
 (2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$   
 (3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$   
 (4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

**Fig. 13. Average forward current as a function of ambient temperature; typical values**



$T_j = 175\text{ °C}$   
 (1)  $\delta = 1$  (DC)  
 (2)  $\delta = 0.5$ ;  $f = 20\text{ kHz}$   
 (3)  $\delta = 0.2$ ;  $f = 20\text{ kHz}$   
 (4)  $\delta = 0.1$ ;  $f = 20\text{ kHz}$

**Fig. 14. Average forward current as a function of solder point temperature; typical values**



8. Test information

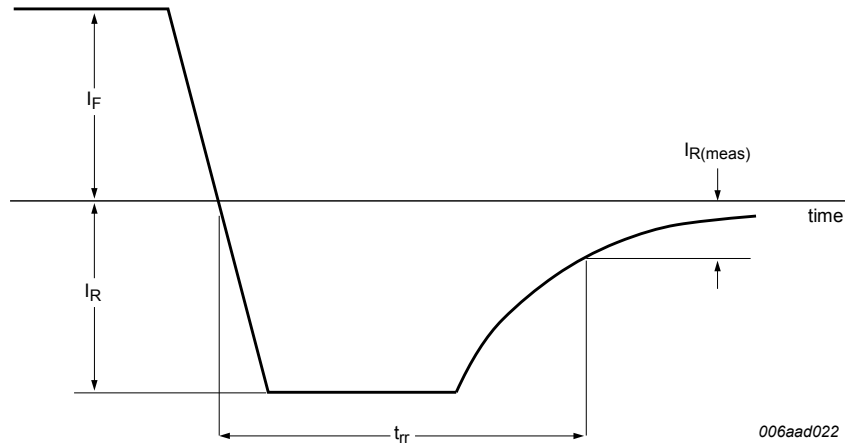


Fig. 15. Reverse recovery definition

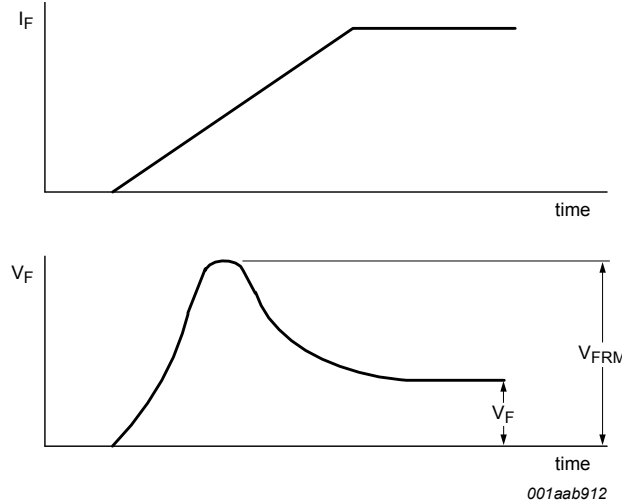


Fig. 16. Forward recovery definition

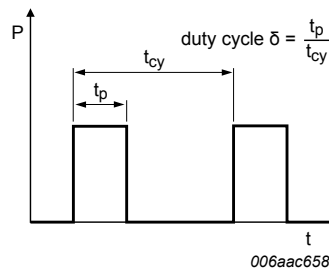


Fig. 17. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations:  
 $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 9. Package outline

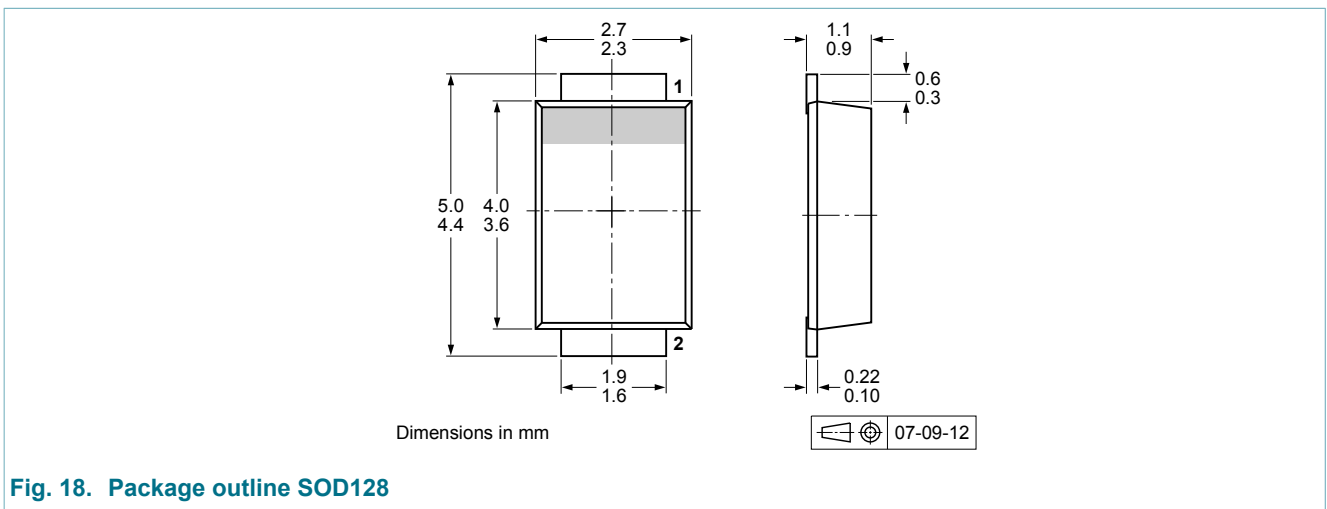


Fig. 18. Package outline SOD128

## 10. Soldering

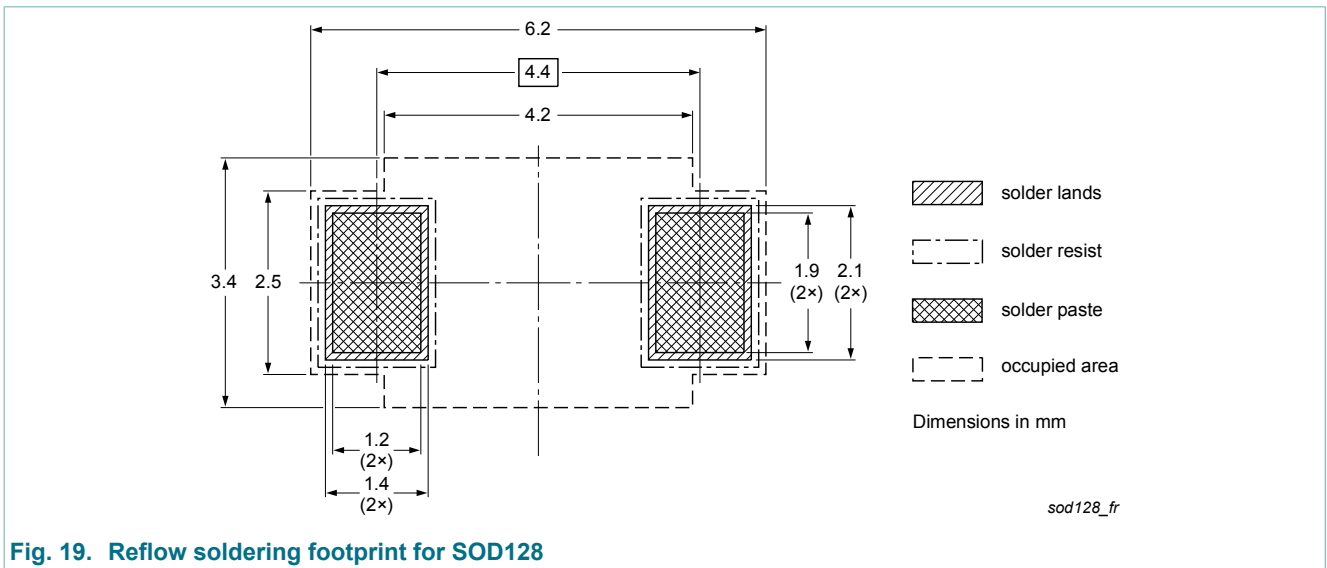


Fig. 19. Reflow soldering footprint for SOD128

## 11. PMEG6030ETP

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6030ETP v.1	20121015	Product data sheet	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 15 October 2012

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